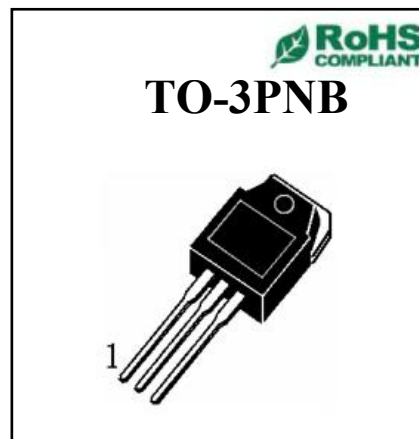


High Voltage Fast-Switching NPN Power Transistor

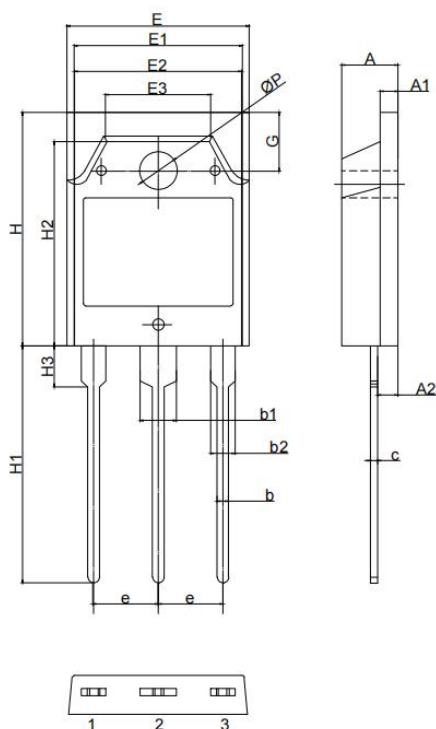
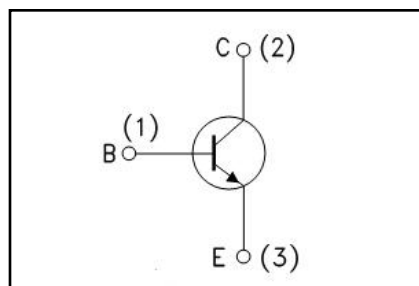
◆ Features:

- ✧ High Switching Speed
开关速度快
- ✧ Low forward voltage drop
正向压降低
- ✧ High efficiency and low power loss
高效低功耗
- ✧ High current surge capability
大电流浪涌能力强



◆ Applications

- ✧ Electronic Ballast
电子镇流器
- ✧ Switching Mode Power Supply
开关电源
- ✧ Motor Controls
电机控制
- ✧ Solenoid/Relay drivers and Deflection circuits applications
电磁阀/继电器驱动器和偏转电路应用



TO-3PNB尺寸表/mm			
Symbol	Min	Nom	Max
A	4.60	4.80	5.00
A1	1.30	1.50	1.60
A2	1.40	1.50	1.60
b	0.80	1.00	1.20
b1	2.90	3.10	3.30
b2	1.90	2.10	2.30
c	0.50	0.60	0.70
e	5.25	5.45	5.65
E	15.20	15.60	16.00
E1	13.20	13.40	13.60
E2	13.10	13.50	13.50
E3	9.10	9.30	9.50
H	19.80	20.00	20.20
H1	20.10	20.30	20.50
H2	18.50	18.70	18.90
H3	3.20	3.50	3.80
G	4.80	5.00	5.20
ØP	3.00	3.20	3.40

◆ Absolute Maximum Ratings (Tc=25°C)

Symbol	Parameters	Ratings	Unit
VCBO	Collector-Base Voltage 集电极 - 基极电压	700	V
VCEO	Collector-Emitter Voltage 集电极 - 发射极电压	400	V
VEBO	Emitter-Base Voltage 发射极 - 基极电压	9	V
I _c	Collector Current-Continuous 集电极连续电流	8	A
I _B	Base Current-Continuous 基极连续电流	4	A
PC	Collector Power Dissipation 耗散功率	125	W
T _j	Max.Operating junction temperature 最大结温	150	°C
T _{stg}	Storage Temperature 存储温度	-55 ~ +150	°C
R _{th(j-c)}	Thermal Resistance, Junction to Case 结到外壳的热阻	1.0	°C/W

◆ Electrical characteristics (Tc=25°C unless otherwise noted)

Symbol	Parameters	Min	Typ	Max	Units	Conditions
I _{CBO}	Collector Cutoff Current 集电极截止电流		--	10	μA	V _{CE} =700V, I _B =0
I _{EBO}	Emitter Cutoff Current 发射极截止电流		--	10	uA	V _{EB} =9V, I _C =0
BV _{CEO}	Collector Emitter Sustaining voltage(Note 1) 集电极发射极持续电压	400			V	I _C =5mA, I _B =0
V _{CE(sat)}	Collector Emitter Saturation Voltage(Note 1) 集电极发射极饱和电压	--	0.3	1.0	V	I _C =5A, I _B =1A
V _{BE(sat)}	Base-Emitter Saturation Voltage(Note 1) 基极发射极饱和电压	--	1.0	1.5	V	I _C =3A, I _B =0.6A
h _{FE}	DC Current Gain(Note 1) 直流电流增益	20	--	35		I _C =2A, V _{CE} =5V
f _T	Current-Gain—Bandwidth 电流增益带宽	4	--	--	MHz	V _{CE} =10V, I _C =0.5A, f=1MHz
T _s	Period of storage 贮存时间	2.0	--	8.0	us	I _C =500mA, UI9600
T _r	Up time 上升时间	--	--	1	us	
T _f	Drop-out time 下降时间	--	--	1	us	

Note 1: Pulse test: PW ≤ 300us , duty cycle ≤ 2%.